MOSFET - Single N-Channel, Small Signal, XLLGA3, 0.62 x 0.62 x 0.4 20 V, 224 mA

Features

- Single N-Channel MOSFET
- Ultra Small and Thin Package (0.62 x 0.62 x 0.4 mm)
- Low R_{DS(on)} Solution in 0.62 x 0.62 mm Package
- 1.5 V Gate Voltage Rating
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V_{DSS}	20	V
Gate-to-Source Voltage			V _{GS}	±8.0	V
Continuous Drain	Steady	T _A = 25°C	Ι _D	224	mA
Current (Note 1)	State	T _A = 85°C		162	
	t ≤ 5 s	T _A = 25°C		241	
Power Dissipa- tion (Note 1)	Steady State	T _A = 25°C	P _D	120	mW
	t ≤ 5 s	T _A = 25°C		139	
Pulsed Drain Current $t_p = 10 \mu s$			I _{DM}	673	mA
Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to 150	°C
Source Current (Body Diode)			I _S	120	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	1040	°C/W
Junction-to-Ambient – t ≤ 5 s (Note 1)	$R_{\theta JA}$	900	

- 1. Surface Mounted on FR4 Board using the minimum recommended pad size, (or 2 $\mbox{mm}^2),$ 1 oz Cu.
- 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%.

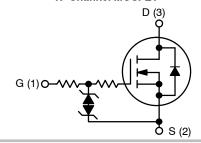


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MOSFET				
V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX		
20 V	1.4 Ω @ 4.5 V			
	1.9 Ω @ 2.5 V	224 mA		
	2.2 Ω @ 1.8 V] 2241111		
	4.3 Ω @ 1.5 V			

N-Channel MOSFET



MARKING DIAGRAM



XLLGA3 CASE 713AB



A = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NTNS3193NZT5G	XLLGA3 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

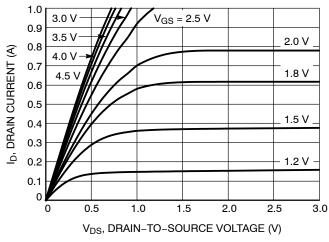
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Units
OFF CHARACTERISTICS		•		<u>.</u>	•		•
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I_D = -250 μA, ref to 25°C			19		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 20 V	T _J = 25°C			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8.0 V				±2.0	μΑ
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, I _D = 250 μA	0.4		1.0	V
Negative Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J				1.9		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 100 mA			0.65	1.4	Ω
		V _{GS} = 2.5 V, I _D = 50 mA			0.9	1.9	1
		V _{GS} = 1.8 \	/, I _D = 20 mA		1.1	2.2	1
		V _{GS} = 1.5 \	/, I _D = 10 mA		1.4	4.3	1
Forward Transconductance	9FS	V _{DS} = 5 V, I _D = 100 mA			0.56		S
Source-Drain Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 10 \text{ mA}$			0.55	1.0	V
CHARGES & CAPACITANCES							
Input Capacitance	C _{ISS}				15.8		pF
Output Capacitance	C _{OSS}	$V_{GS} = 0 \text{ V, f} = 1 \text{ MHz,} $ $V_{DS} = 15 \text{ V}$			3.5		1
Reverse Transfer Capacitance	C _{RSS}				2.4		1
Total Gate Charge	Q _{G(TOT)}	V_{GS} = 4.5 V, V_{DS} = 15 V, I_{D} = 200 mA			0.70		nC
Threshold Gate Charge	Q _{G(TH)}				0.05		1
Gate-to-Source Charge	Q _{GS}				0.14		
Gate-to-Drain Charge	Q_{GD}				0.10		1
SWITCHING CHARACTERISTICS, VG	S = 4.5 V (Note 3)						
Turn-On Delay Time	t _{d(ON)}				18		ns
Rise Time	t _r	V_{GS} = 4.5 V, V_{DD} = 15 V, I_D = 200 mA, R_G = 2 Ω			35		1
Turn-Off Delay Time	t _{d(OFF)}				201		1
Fall Time	t _f				110		1

^{3.} Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

1.0

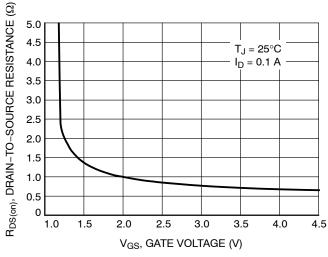


 $V_{DS} = 5 V$ 0.9 $T_J = 25^{\circ}C$ 0.8 DRAIN CURRENT (A) = 125°C 0.7 0.6 0.5 0.4 0.3 ؽ 0.2 0.1 0 0.5 1.0 1.5 2.0 2.5 3.0 V_{GS}, GATE-TO-SOURCE VOLTAGE (V)

 $T_J = -55^{\circ}C$

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



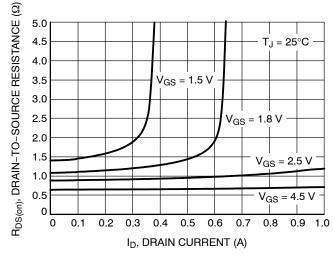
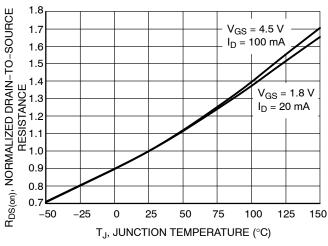


Figure 3. On-Resistance vs. Gate-to-Source Voltage

Figure 4. On-Resistance vs. Drain Current and Gate Voltage



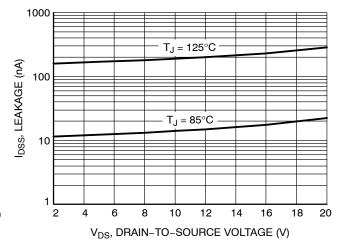
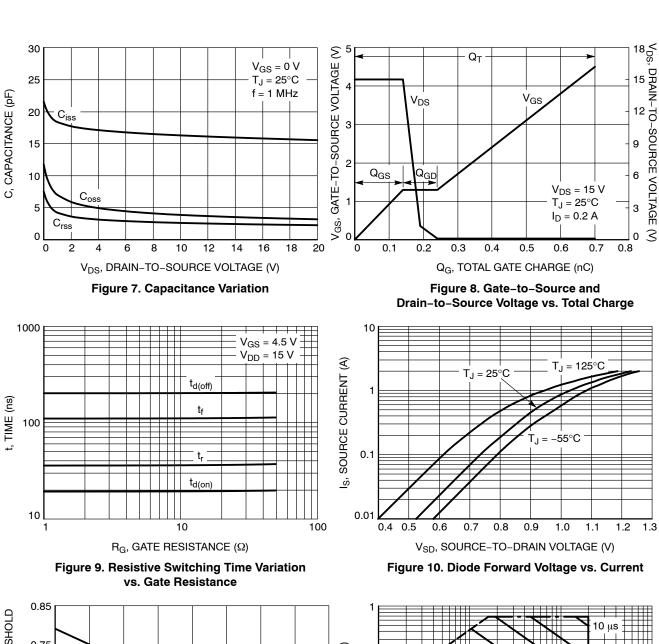


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS



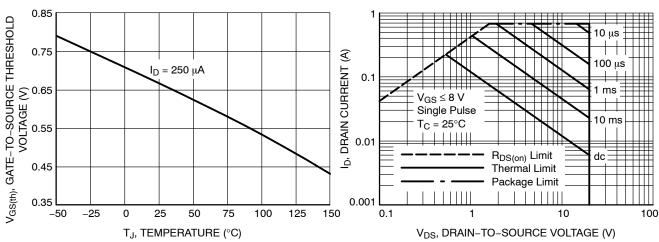


Figure 11. Threshold Voltage

Figure 12. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS

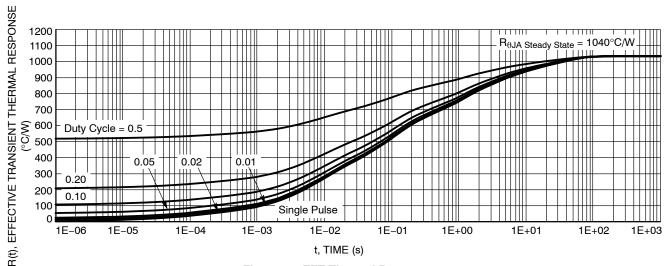
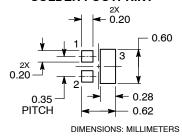


Figure 13. FET Thermal Response

MINIMUM RECOMMENDED SOLDER FOOTPRINT*



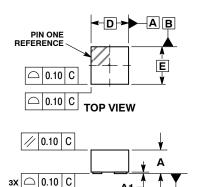
^{*}Dependent upon end user capabilities, this footprint could be used as a minimum.



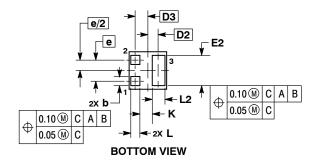


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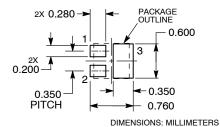


SIDE VIEW



C SEATING PLANE

RECOMMENDED SOLDER FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.340	0.440		
A1	0.000	0.030		
b	0.100 0.200			
D	0.620	BSC		
D2	0.175 BSC			
D3	0.205 BSC			
E	0.620 BSC			
E2	0.400 0.600			
е	0.350 BSC			
K	0.200 REF			
L	0.090	0.210		
L2	0.110	0.310		

GENERIC MARKING DIAGRAM*



Х = Specific Device Code

Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

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